

**INFORMATION DISCLOSURE
CITATION IN AN
I P E APPLICATION**

A circular stamp with the words "U.S. PATENT & TRADEMARK OFFICE" around the perimeter. The center contains the date "DEC 1 8 2003".

(PTO-1449)

ATTY. DOCKET NO.
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FILING DATE
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GROUP 2825

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<i>BK</i>		C.F. Lin et al., "Improved Contact Performance of GaN Film Using Si Diffusion", 2000 American Institute of Physics, Applied Physics Letters, Vo. 76, No. 14, pp. 1878-1880, April 3, 2000
<i>VZL</i>		Hiroyuki MASATO et al., "Novel High Drain Breakdown Voltage AlGaN/GaN HfETs Using Selective Thermal Oxidation Process", IEEE, IEDM 16.2.1-16.2.4, pp. 377-380, 2000

***EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered.
Include copy of this form with the reference cited.

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1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English-Incubus Translation is attached.